

N-channel TrenchMOS logic level FET Rev. 3 — 9 November 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

	quientienterentere					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	32	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	77	W
Static cha	racteristics					
R _{DSon} drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	28	33	mΩ	
	resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{I}};$ see $\frac{\text{Figure } 12}{\text{I}}$	-	31	37	mΩ

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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 32 \text{ A}; V_{sup} \leq 30 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	76	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 V; I_D = 15 A;$ $V_{DS} = 44 V; T_j = 25 °C;$ see <u>Figure 13</u>	-	9.2	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	_	
2	D	drain ^[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make connection to pin 2 of the SOT428 package.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9237-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

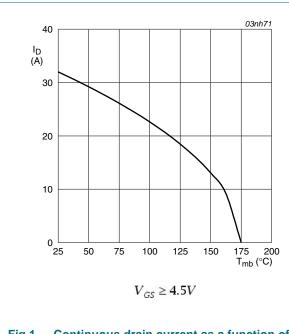
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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	32	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	22	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C; } t_p \le 10 \mu\text{s; pulsed;}$ see <u>Figure 3</u>	-	129	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	77	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	32	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	129	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 32 \text{ A}; V_{sup} \le 30 \text{ V}; R_{GS} = 50 \Omega;$ V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	76	mJ





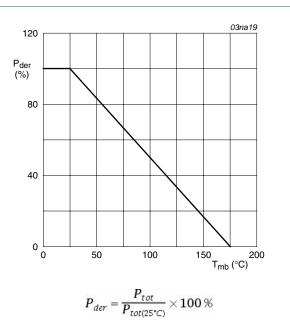
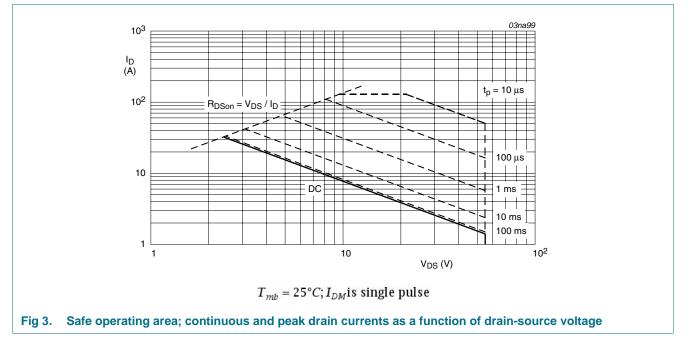


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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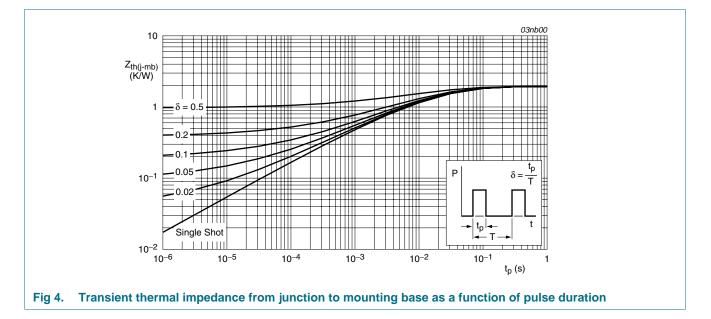
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Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	1.94	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W



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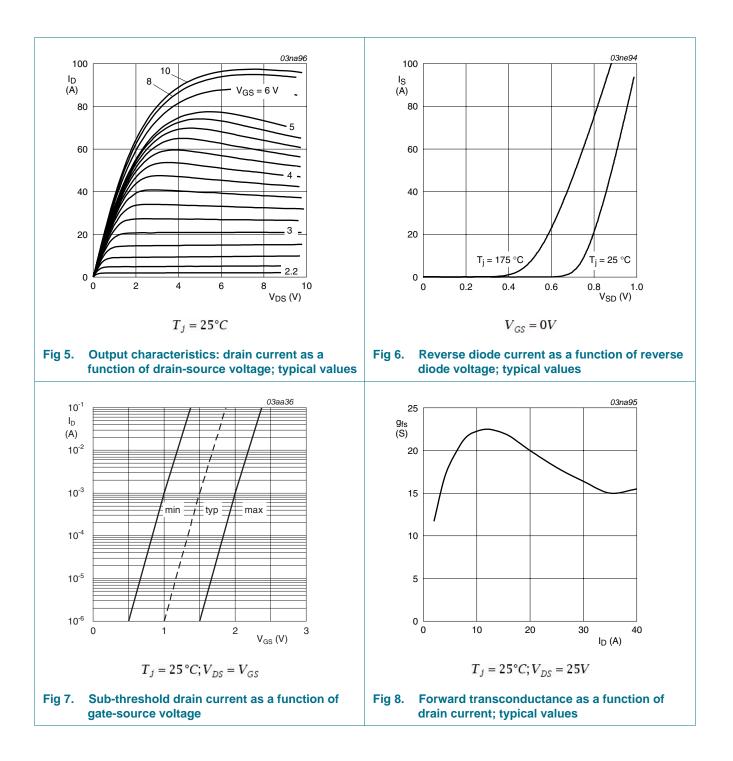
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6. Characteristics

	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V _{GS(th)} gate-source voltage	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10</u>	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 °C$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C	-	-	38	mΩ
	resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	74	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	28	33	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	31	37	mΩ
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$	-	17.6	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	2.9	-	nC
Q _{GD}	gate-drain charge		-	9.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	927	1236	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	151	181	pF
C _{rss}	reverse transfer capacitance		-	96	131	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	95	-	ns
t _f	fall time		-	73	-	ns
L _D	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-dra	ain diode					
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	42	-	ns
Qr	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	83	-	nC
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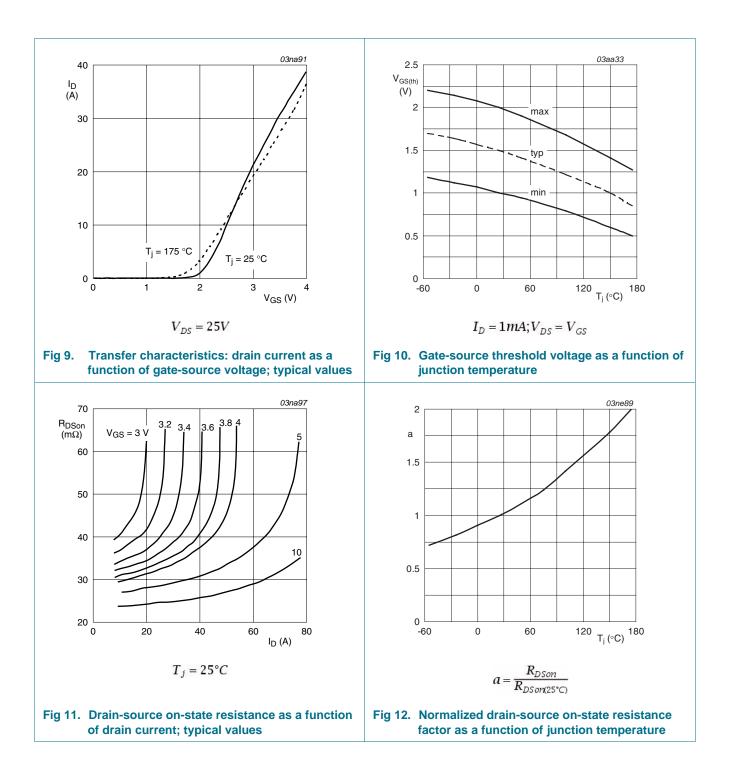
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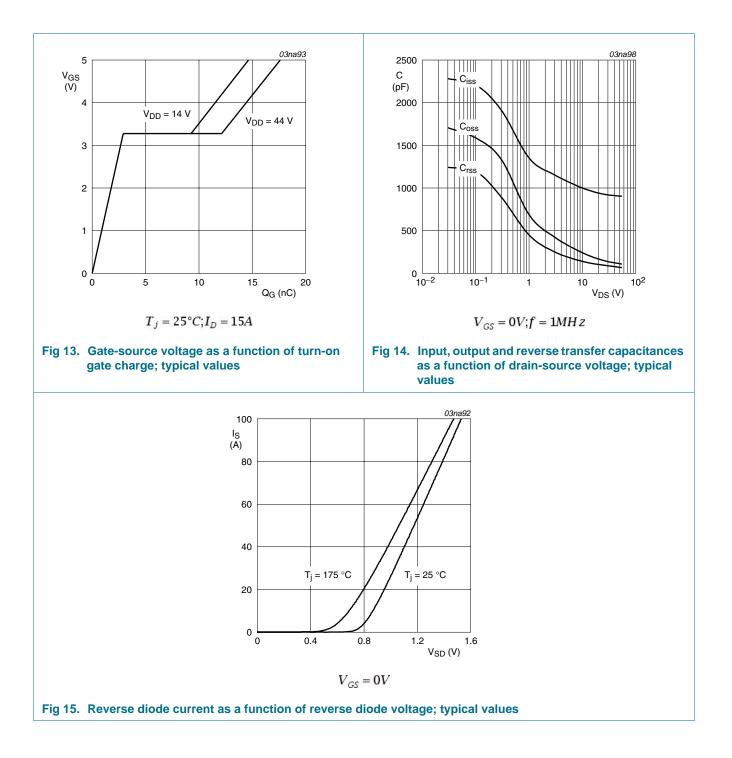
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Package outline 7.

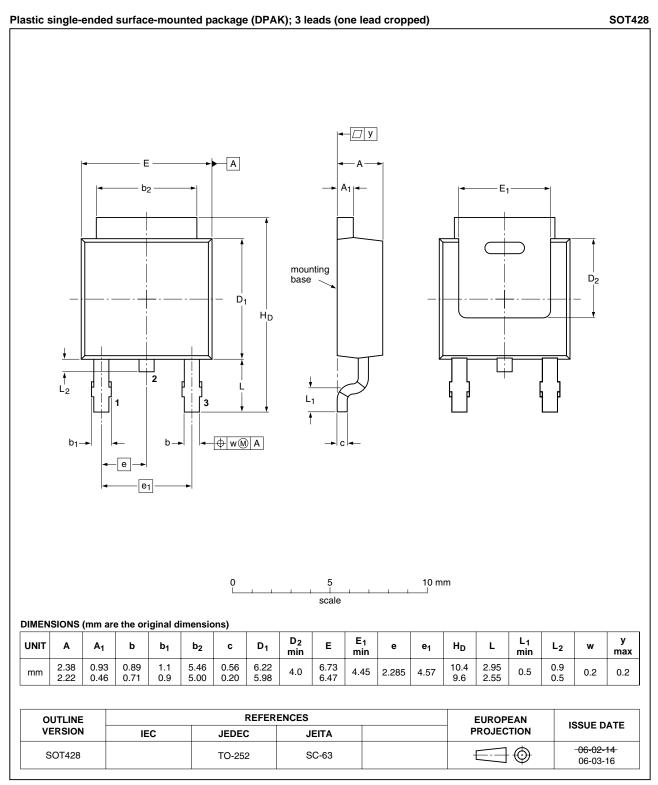


Fig 16. Package outline SOT428 (DPAK)

BUK9237-55A **Product data sheet**

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8. Revision history

Document ID	Release date	Data sheet status		
		Data Sheet Status	Change notice	Supersedes
BUK9237-55A v.3	20101109	Product data sheet	-	BUK9237_55A-02
Modifications:	 Various chang 	ges to content.		
	 The format of of NXP Semic 	this data sheet has been rec conductors.	lesigned to comply with	the new identity guidelines
	 Legal texts hat 	we been adapted to the new	company name where	appropriate.
BUK9237_55A-02	20020214	Product specification	-	BUK9237_55A-01

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9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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